

PGA26E19BA

# **Product Standards**

PGA26E19BA

Established: 2014-09-25 Revised: 2019-03-07 Page 1 of 12

### **Panasonic**

#### PGA26E19BA

Туре	GaN-Tr			
Application	or power switching			
Structure	N-channel enhancement mode FET			
Equivalent Circuit	Figure 1			
Out Line	DFN 8X8	Marking	PGA26E19	

A. ABSOLUTE MAXIMUM RATINGS (Tj = 25 °C, unless otherwise specified)

	A. ABSOLUTE MAXIMUM RATINGS ( I):		Values				N	
No.	Item	Symbol	Min.	Тур.	Max.	Unit	Note	
1	Drain-source voltage ( DC ) *1	VDSS	1	-	600	٧		
2	Drain-source voltage ( pulse ) *2	VDSP	-	-	750	V	The state of	
3	Gate-source voltage ( DC ) *1	VGSS	-10		-	٧	*VGSS+ is given by IG ratings *See application note	
4	Gate current ( DC ) *1	IG			19	mA	*See application note	
5	Gate current ( pulse ) *3,4	IGP	-	-	0.6	\ Adill	*See application note	
6	Electric gate charge ( pulse )	QGP	-		12	nC	*f=200kHz *See application note	
7	Drain current ( DC ) ( Tc = 25 °C ) *1	ID		- 40	15	A	Figure 4	
8	Drain reverse current ( DC ) ( Tc = 25 °C ) *1	IDR	-	diges.	15	Α		
9	Drain current ( pulse )*5 ( Tc = 25 °C )*1	ID pulse	i balin	SUCE DI	23	Α	Figure 4	
10	Drain reverse current ( pulse )*5 ( Tc = 25 °C )*1	IDR pulse	Milli Million	-	23	Α		
11	Power dissipation (Tc = 25°C)	PD	ک <sup>ہ</sup> ۔	-	83	W	Figure 2	
12	Junction temperature		-55	-	150	°C		
13	Storage temperature	Tstg	-55	-	150	°C		
14	Drain-source voltage slope	dv/dt	-	-	200	V/ns		

#### [Special instructions]

- \*1 : Please use this product to meet a condition of Tj within 150  $^{\circ}\text{C}.$
- $^{*}2$ : Spike duty cycle D < 0.1, spike duration < 1us, total spike time < 1hour.
- \*3 : IGP is defined as (Vcc Vplateau) / Rgon, as shown in Figure A. Vplateau is the voltage between Gate and Kelvin Source.
- \*4 : Please use this product to meet both a maximum gate current and a maximum gate pulse charge of IGP(0.6A) and Q(12nC) respectively, as shown in Figure H.
- \*5 : Pulse width limited by Tjmax.

Established: 2014-09-25 Revised: 2019-03-07 Page 2 of 13

### **Panasonic**

### PGA26E19BA

B. ELECTRICAL CHARACTERISTICS ( Tj = 25  $^{\circ}C$  , unless otherwise specified )

No.	Item	Symbol	Measurement Condition	Min.	Тур.	Max.	Unit
1	Drain cut-off current	IDSS	VDS=600 V, VGS=0 V, Tj=25 °C	-	-	39	μA
I Diamic	Brain cut-on current	ססםו	VDS=600 V, VGS=0 V, Tj=150 °C	-	39	-	μΑ
2	Gate-source leakage current	IGSS	VGS=-3 V VDS=0 V	-1	-	-	μΑ
3	Gate forward voltage	VGSF	IGS=10 mA open drain	2.8	3.5	4.2	V
4	Gate threshold voltage	VTH	VDS=10 V IDS=1 mA	0.9	1.2	1.6	V
5	Drain-source on-state resistance	RDS(on)	IGS=10 mA, IDS=5 A, Tj=25 °C		140	190	mΩ
	Drain source on claic resistance	TtD (OII)	IGS=10 mA, IDS=5 A, Tj=150 °C	-	290	illips.	mΩ
6	Gate resistance	RG	f=100MHz open drain	(SC)/C/C	0.8	-	Ω
7	Transfer conductance	gfs	VDS=8 V IDS=5 A	14/50	15	-	S
8	Input capacitance	Ciss	VDS=400 V VGS=0 V	-	160	-	pF
9	Output capacitance	Coss		-	28	-	pF
10	Reverse transfer capacitance	Crss	f=1 MHz		0.2	-	pF
11	Turn-on delay time	td(on)	VDD=400 V	-	3.4	-	ns
12	Rise time	tr	IDS=5 A (Figure A, Figure B) Vcc=12 V Rgon=15 Ω, Rgoff=4.7 Ω,	ı	5.2	-	ns
13	Turn-off delay time	td(off)		-	3.4	-	ns
14	Fall time	il di	Rig=1500 Ω, Cs=680 pF	-	2.4	-	ns
15	Effective output capacitance ( energy related )	Co(er)	VDC 0 490 V	-	33	-	pF
16	Effective output capacitance ( time related )	Co(tr)	VDS=0-480 V	-	37	-	pF

Established: 2014-09-25 Page 3 of 13 Revised: 2019-03-07

Established: 2019-12-02

Downloaded from Arrow.com

### **Panasonic**

### PGA26E19BA

C. GATE CHARGE CHARACTERISTICS (Tj = 25 °C, unless otherwise specified)

C. GA	C. GATE CHARGE CHARACTERISTICS (T) = 25 °C, utiless otherwise specified)						
No.	Item	Symbol	Measurement Condition	Min.	Тур.	Max.	Unit
1	Gate charge	Qg	VDD=400 V IDS=5 A (Figure C. Figure D)	-	2.0	-	nC
2	Gate-source charge	Qgs		-	0.3	-	nC
3	Gate-drain charge	Qgd	(Figure C, Figure D)		1.0	-	nC
4	Gate plateau voltage	V plateau	VDD=400 V IDS=5 A	-	1.8	-	V

D. REVERSE CONDUCTING CHARACTERISTICS (Ti = 25 °C, unless otherwise specified)

D. INE	b. REVEROE COMPOCITION CHARACTERIOTICS (1) = 23 °C, diffess office wise specified)							
No.	Item	Symbol	Measurement Condition	Min.	Тур.	Max.	Unit	
1	Source-drain forward voltage	VSD	VGS=0 V ISD=5 A	1	2.6	IIIII	٧	
2	Reverse recovery charge	Qrr			00	ı	nC	
3	Reverse recovery time	trr	VDS=400 V	I. O.	0		ns	
4	Peak reverse recovery current	Irrm	ISD=5 A	) )_	0	-	Α	
5	Output charge	Qoss	wing discolling	1	17		nC	

#### E. THERMAL RESISTANCE CHARACTERISTICS

No.	Item	Symbol	Measurement Condition	Min.	Тур.	Max.	Unit
1	Thermal resistance ( junction to case )	Rth(j-c)	They will be	-	-	1.5	°C/W
2	Thermal resistance ( junction to ambient ) *1	Rth(j-a)	differ	-	-	46	°C/W
3	Reflow soldering temperature	Tsold	reflow MSL3	-	-	260	°C

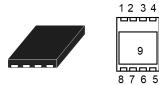
#### [Notes]

\*1 : Device mounted on four layers epoxy PCB (6.45  $\text{cm}^2$  copper area and 70  $\mu \text{m}$  thickness).

Established: 2014-09-25 Revised: 2019-03-07 Page 4 of 13

Established: 2019-12-02

Downloaded from Arrow.com.



Top View

Bottom View

1,2.3,4 : Drain5,6,9 : Source7 : Kelvin Source

■ Equivalent circuit / Electrical characteristics

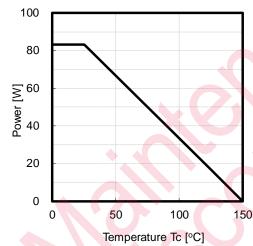
8 : Gate

G SKO S

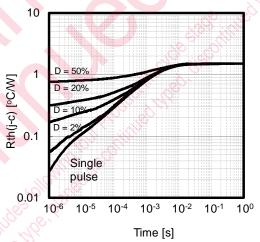
Notice:

Please connect SK pin to gate driver.

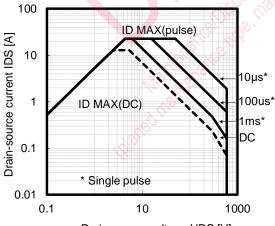
#### [Figure 1: Pin layout / Equivalent circuit]



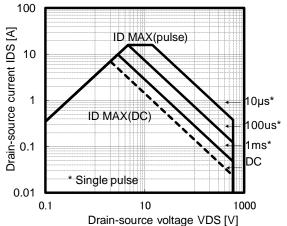
[Figure 2: Max. power dissipation]



[Figure 3: Transient thermal impedance]



Drain-source voltage VDS [V] [Figure 4: Safe operating area Tc = 25 °C]

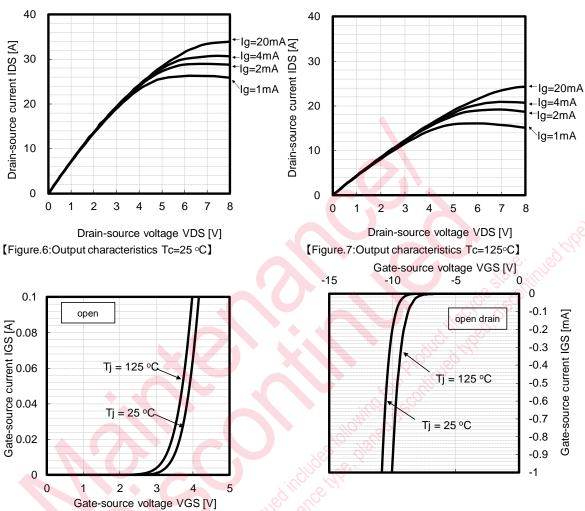


[Figure 5: Safe operating area Tc = 125 °C]

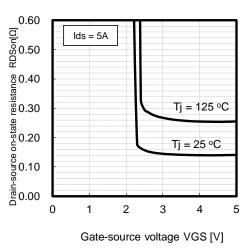
Established: 2014-09-25 Revised: 2019-03-07 Page 5 of 13

### **Panasonic**

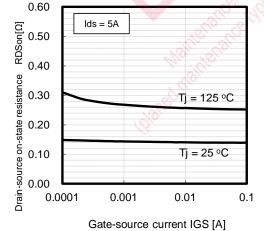
#### PGA26E19BA







[Figure.9:Gate characteristics]

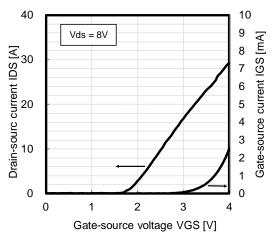


[Figure 10:Drain-source on-state resistance(RDS(on)-IGS)] [Figure.11:Drain-source on-state resistance(RDS(on)-VGS)]

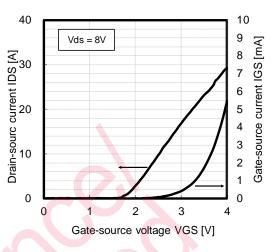
Established: 2014-09-25 Revised: 2019-03-07 Page 6 of 13

### **Panasonic**

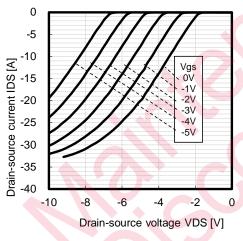
#### PGA26E19BA



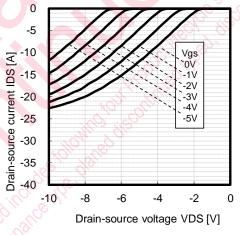
[Figure 12:Transfer characteristics (Tc=25°C)]



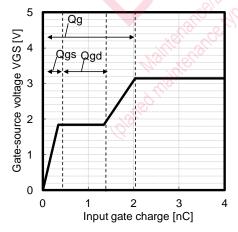
[Figure 13:Transfer characteristics (Tc=125°C)]



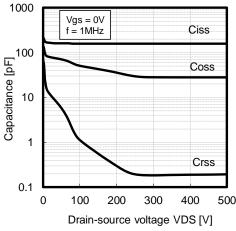
[Figure.14:Reverse channel characteristics (Tc=25°C)]



[Figure.15:Reverse channel characteristics (Tc=125°C)]



[Figure 16:Gate charge characteristics]

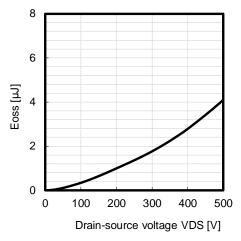


[Figure 17:Capacitance characteristics]

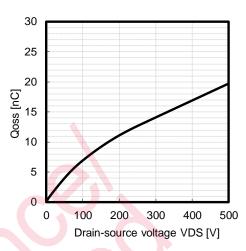
Established: 2014-09-25 Revised: 2019-03-07 Page 7 of 13

## **Panasonic**

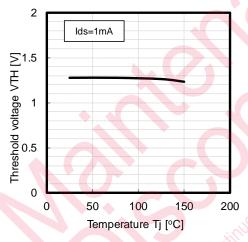
### PGA26E19BA



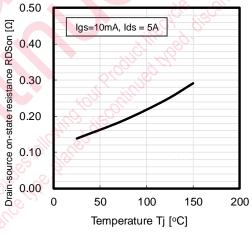
[Figure 18:Output capacitance stored energy]



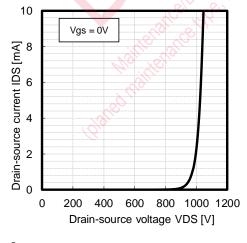
[Figure 19:Output charge]



[Figure.20:Threshold voltage (VTH-Tj)]



[Figure 21:Drain-source on-state resistance(RDS(on)-Tj)]

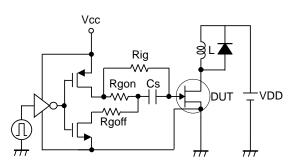


[Figure.22:Drain-Source leakage current (Tc=25°C)]

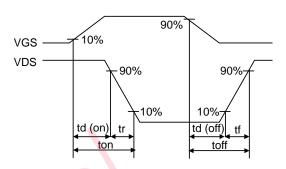
Established: 2014-09-25 Revised: 2019-03-07 Page 8 of 13

### **Panasonic**

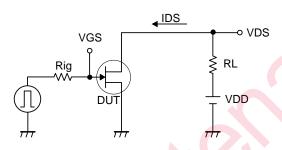
#### PGA26E19BA



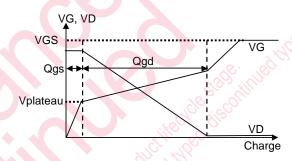
[Figure A : Switching time measurement]



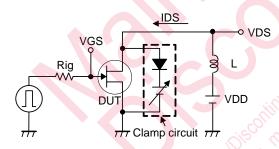
[Figure B : Switching wave form]



[Figure C : Gate charge measurement]



[Figure D : Gate charge wave form]



(Figure E : Reverse bias safe operating area dv/dt measurement circuit)

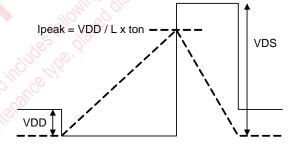
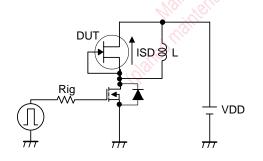
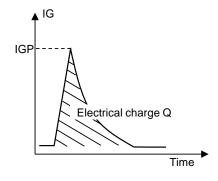


Figure F : Reverse bias safe operating area dv/dt wave form



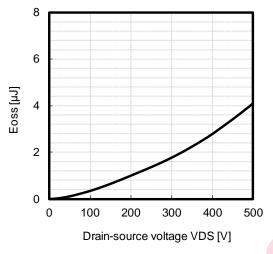
[Figure G : di/dt measurement circuit]



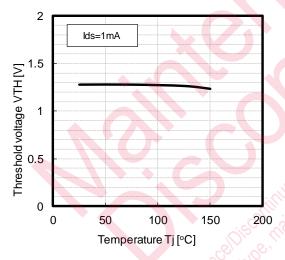
[Figure H: IGP wave form]

Established: 2014-09-25 Revised: 2019-03-07 Page 9 of 13

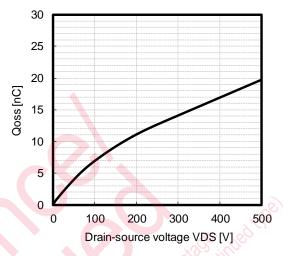
### **Panasonic**



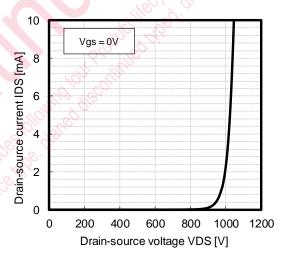
[Figure 17:Output capacitance stored energy]



[Figure.19:Threshold voltage (VTH-Tj)]



[Figure 18:Output charge]



[Figure.20:Drain-Source leakage current (Tc=25°C)]

Established: 2014-09-25 Revised: 2019-03-07 Doc No. TD4-ZZ-01675 Revision. 2

Revision. 008

### nasonic

PGA26E19BA

#### [Precautions for Use]

- The product has risks for break-down or burst or giving off smoke in following conditions. Avoid the following use. Fuse should be added at the input side or connect zener diode between Gate pin and GND, etc as a countermeasure to pass regulatory Safety Standard. Concrete countermeasure could be provided individually. However, customer should make the final judgment.
  - (1) Reverse the Drain pin and gate pin connection to the power supply board.
  - (2) Drain pin short to Kelvin Source pin and Source pin.
  - (3) Drain pin short to Gate pin.
  - (4) Gate pin open.
- This product is under development and is subject to change without notice standards.

2014-09-25 Page 11 of 13 Established: Revised: 2019-03-07

Established: 2019-12-02 Downloaded from Arrow.com.

## **Panasonic**

### PGA26E19BA

Outline

Unit: mm D ដ D2 **DIMENSION** SYMBOL MIN NOM MAX Α 1.15 1.25 1.35 A1 0.00 0.02 0.05 A2 0.40 0.50 0.60 b 0.90 1.00 1.10

D

D1

D2

Е

E1

E2

E3

e L 7.90

6.84

0.40

7.90

0.90

3.10

2.70

0.40

8.00

6.94

0.50

8.00

1.00

3.20

2.80

2.00 B.S.C.

0.50

8.10

7.04

0.60

8.10

1.10

3.30

2.90

0.60

Established: 2014-09-25 Page 12 of 13 Revised: 2019-03-07

<sup>\*</sup>Please note that technical specifications are subject to change without notice.

Doc No. TD4-ZZ-01675 Revision. 2

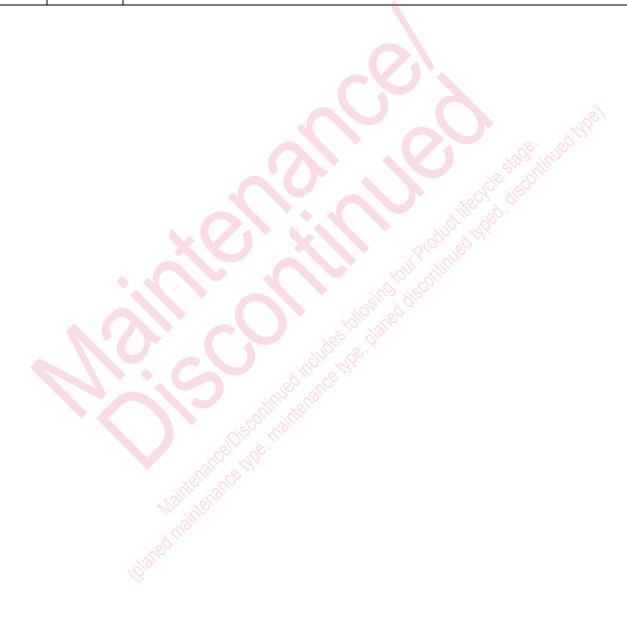
Revision. 008

### **Panasonic**

PGA26E19BA

■ Revision History

Revision No	Date	Description of change
007	2017-01-24	1st edition
800	2019-03-07	Drain current(DC), Power dissipation, Thermal resistance (junction to case), Pin name, Symbol mark, Safe operation area, Output characteristics, Transfer characteristics



Established: 2014-09-25 Page 13 of 13 Revised: 2019-03-07

Established: 2019-12-02

Downloaded from Arrow.com.

# Request for your special attention and precautions in using the technical information and semiconductors described in this book

- (1) If any of the products or technical information described in this book is to be exported or provided to non-residents, the laws and regulations of the exporting country, especially, those with regard to security export control, must be observed.
- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products. No license is granted in and to any intellectual property right or other right owned by Panasonic Corporation or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information de-scribed in this book.
- (3) The products described in this book are intended to be used for general applications (such as office equipment, communications equipment, measuring instruments and household appliances), or for specific applications as expressly stated in this book.
  - Please consult with our sales staff in advance for information on the following applications, moreover please exchange documents separately on terms of use etc.: Special applications (such as for in-vehicle equipment, airplanes, aerospace, automotive equipment, traffic signaling equipment, combustion equipment, medical equipment and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
  - Unless exchanging documents on terms of use etc. in advance, it is to be understood that our company shall not be held responsible for any damage incurred as a result of or in connection with your using the products described in this book for any special application.
- (4) The products and product specifications described in this book are subject to change without notice for modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most upto-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.
- (5) When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful not to exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
  Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages,
- (6) Comply with the instructions for use in order to prevent breakdown and characteristics change due to external factors (ESD, EOS, thermal stress and mechanical stress) at the time of handling, mounting or at customer's process. We do not guarantee quality for disassembled products or the product re-mounted after removing from the mounting board. When using products for which damp-proof packing is required, satisfy the conditions, such as shelf life and the elapsed time since first opening the packages.
- (7) When reselling products described in this book to other companies without our permission and receiving any claim of request from the resale destination, please understand that customers will bear the burden.
- (8) This book may be not reprinted or reproduced whether wholly or partially, without the prior written permission of our company.

No.010618

for example, by using the products.